

LOW-VOLTAGE 12-BIT 1-OF-2 FET MULTIPLEXER/DEMULTIPLEXER WITH INTERNAL PULLDOWN RESISTORS

SCDS055G – MARCH 1998 – REVISED APRIL 1999

- 4-Ω Switch Connection Between Two Ports
- Isolation Under Power-Off Conditions
- Make-Before-Break Feature
- Internal 500-Ω Pulldown Resistors to Ground
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Package Options Include Plastic Thin Shrink Small-Outline (DGG), Thin Very Small-Outline (DGV), and 300-mil Shrink Small-Outline (DL) Packages

description

The SN74CBTLV16292 is a 12-bit 1-of-2 high-speed FET multiplexer/demultiplexer. The low on-state resistance of the switch allows connections to be made with minimal propagation delay.

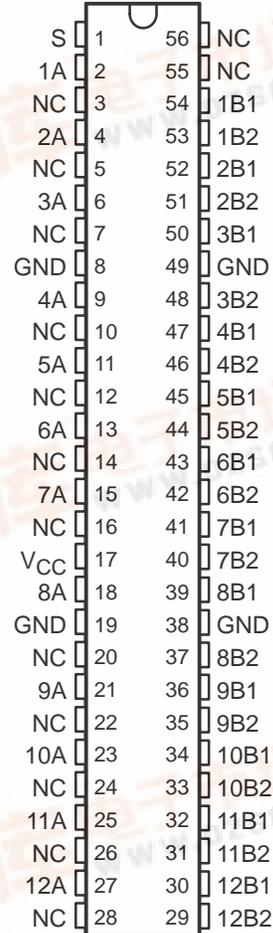
When the select (S) input is low, port A is connected to port B1 and R_{INT} is connected to port B2. When S is high, port A is connected to port B2 and R_{INT} is connected to port B1.

The SN74CBTLV16292 is characterized for operation from -40°C to 85°C.

FUNCTION TABLE

INPUT S	FUNCTION
L	A port = B1 port R_{INT} = B2 port
H	A port = B2 port R_{INT} = B1 port

DGG, DGV, OR DL PACKAGE (TOP VIEW)



NC – No internal connection

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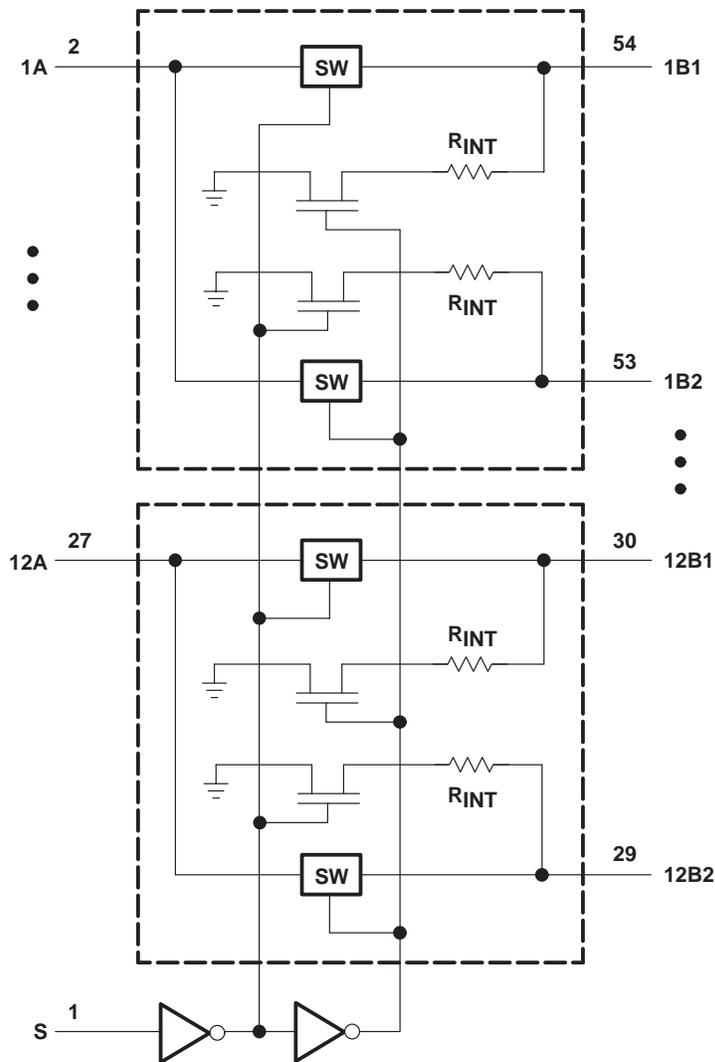


PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

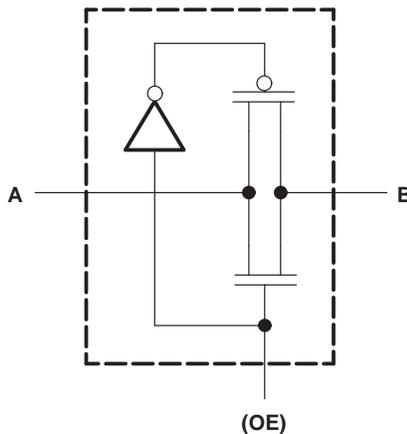
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logic diagram (positive logic)



simplified schematic, each FET switch



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switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	
t _{pd} [†]	A or B	B or A	0.15		0.15		ns
t _{pd} [‡]	S	A	2.5	7.1	2.5	6.7	ns
t _{en}	S	B	1	5.6	1	5	ns
t _{dis}	S	B	1	5	1	4.5	ns

[†] The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance when driven by an ideal voltage source (zero output impedance).

[‡] This propagation delay was measured by observing the change of voltage on the A output introduced by static levels equal to 3-V or 0 for 3.3 V ± 0.3 V or V_{CC} or 0 for 2.5 V ± 0.2 V on B1 and B2 to achieve the desired transition.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	DESCRIPTION	V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		UNIT
		MIN	MAX	MIN	MAX	
t _{mhb} [§]	Make-before-break time	0	2	0	2	ns

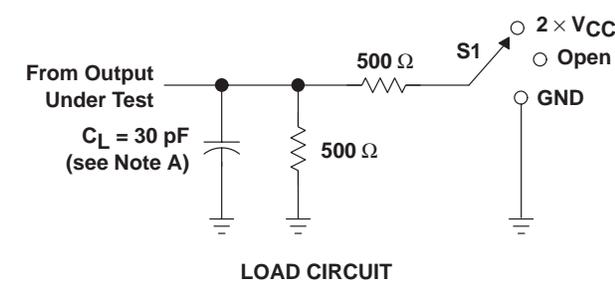
[§] The make-before-break time is the time interval between make and break, during the transition from one selected port to the other.

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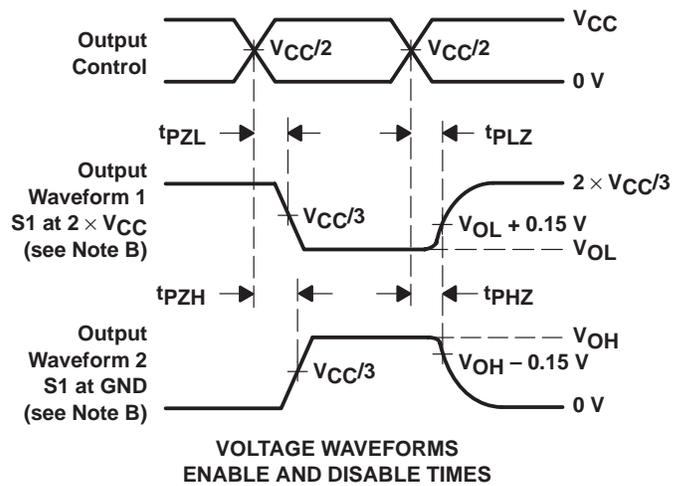
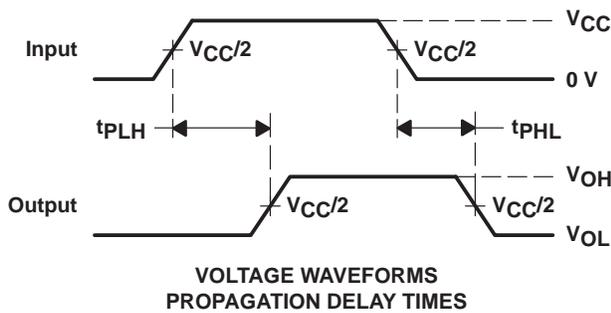
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PARAMETER MEASUREMENT INFORMATION

$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$



TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	$2 \times V_{CC}$
t_{PHZ}/t_{PZH}	GND



- NOTES:
- A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, $Z_O = 50 \Omega$, $t_r \leq 2$ ns, $t_f \leq 2$ ns.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - F. t_{PZL} and t_{PZH} are the same as t_{en} .
 - G. t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 1. Load Circuit and Voltage Waveforms

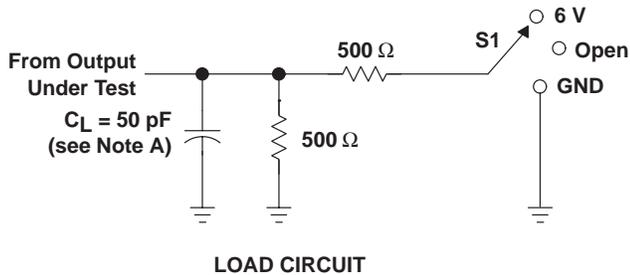
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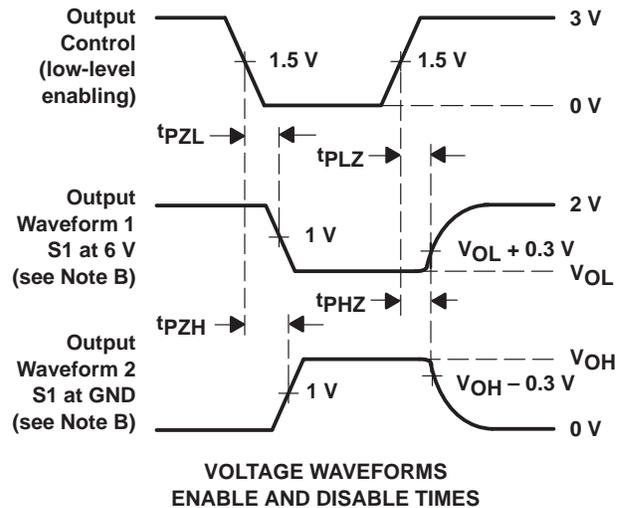
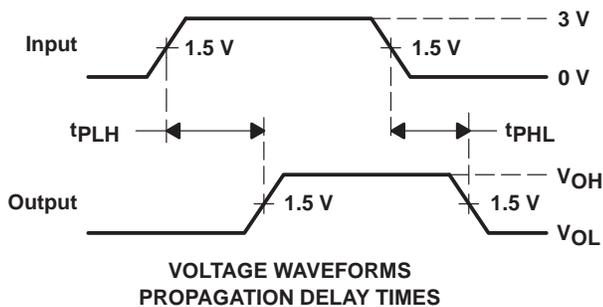
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PARAMETER MEASUREMENT INFORMATION

$$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$$



TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



- NOTES:
- A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
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 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - F. t_{PZL} and t_{PZH} are the same as t_{en} .
 - G. t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 2. Load Circuit and Voltage Waveforms

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